

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re PATENT APPLICATION OF

Inventor(s): YAMAGATA et al.

Filed: Herewith

Title: SUBSTRATE MATERIAL FOR MOUNTING A SEMICONDUCTOR DEVICE,  
SUBSTRATE FOR MOUNTING A SEMICONDUCTOR DEVICE, SEMICONDUCTOR  
DEVICE, AND METHOD OF PRODUCING THE SAME

August 10, 2001

**PRELIMINARY AMENDMENT**

Hon. Commissioner of Patents  
Washington, D.C. 20231

Sir:

Please amend this application as follows:

**IN THE SPECIFICATION:**

At the top of the first page, just under the title, insert:

1.     --This is a    Continuation-In-Part        Divisional  
             Continuation        Substitute Application (MPEP 201.09) of  
    1(a)    National Application No. 09/692,162 filed October 20, 2000, which is a Divisional of  
Appln. No. 08/874,543, filed June 13, 1997
- 1(b)    International Application No. PCT/\_\_\_/  
filed \_\_\_ which designated the U.S.--

2.     --This application claims the benefit of U.S. Provisional Application No.  
60/\_\_\_, filed \_\_\_.--

Respectfully submitted,

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In re PATENT APPLICATION OF

Confirmation No.:

YAMAGATA et al.

Group Art Unit: (Unknown)

Divisional of: 09/692,162

Examiner: (Unknown)

Parent Filed: October 20, 2000

#5/B  
J. Ladd  
9/3/02

Divisional Filed: August 10, 2001

Title: SUBSTRATE MATERIAL FOR MOUNTING  
A SEMICONDUCTOR DEVICE, SUBSTRATE  
FOR MOUNTING A SEMICONDUCTOR DEVICE,  
SEMICONDUCTOR DEVICE, AND METHOD  
OF PRODUCING THE SAME

August 10, 2001

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**PRELIMINARY AMENDMENT**

Hon. Commissioner of Patents  
Washington, D.C. 20231

Sir:

Please preliminarily amend the above-identified Application as follows.

**IN THE SPECIFICATION:**

Page 1, line 13, change the paragraph to read:

*B1*  
2. Description of the Prior Art

*B2*  
Page 1, lines 14-21, change the paragraph to read:

With the recent remarkable increases of the processing rate of semiconductor devices and the degree of integration in semiconductor devices, the heat generated by semiconductor elements has come to produce influences that are not negligible. As a result, substrate materials for mounting semiconductor devices have come to be required to have a high thermal conductivity for efficiently removing the heat generated by semiconductor elements.

*B3*  
Page 9, lines 21-26, change the paragraph to read:

Aluminum/silicon carbide composite alloys have a high degree of hardness.

Therefore it is very difficult to form a shape, especially a complex shape such as heatsink by